STB28NM60ND, STF28NM60ND, STP28NM60ND, STW28NM60ND

N-channel 600 V, 0.13 Ω typ., 23 A FDmesh™ II Power MOSFETs in D²PAK, TO-220FP, TO-220 and TO-247 packages

Datasheet - production data

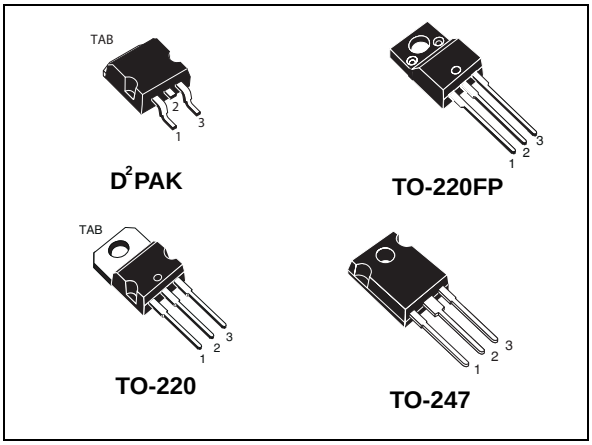
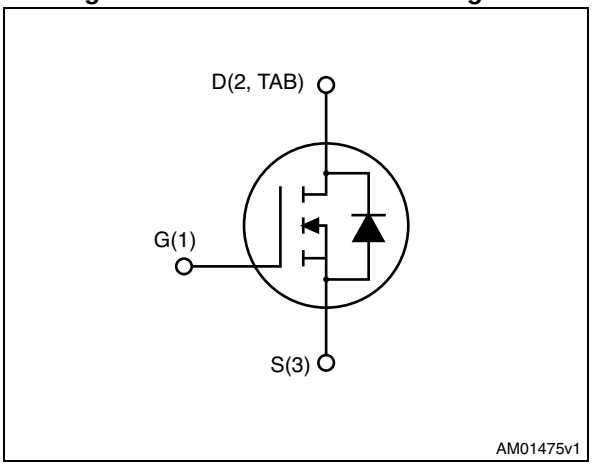


Figure 1. Internal schematic diagram



Features

Order codes	V_{DS} @ $T_{J\ max.}$	$R_{DS(on)\ max}$	I_D
STB28NM60ND	650 V	0.150 Ω	23 A
STF28NM60ND			
STP28NM60ND			
STW28NM60ND			

- Intrinsic fast-recovery body diode
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Extremely high dv/dt and avalanche capabilities

Applications

- Switching applications

Description

These FDmesh™ II Power MOSFETs with intrinsic fast-recovery body diode are produced using the second generation of MDmesh™ technology. Utilizing a new strip-layout vertical structure, these revolutionary devices feature extremely low on-resistance and superior switching performance. They are ideal for bridge topologies and ZVS phase-shift converters.

Table 1. Device summary

Order codes	Marking	Packages	Packaging
STB28NM60ND	28NM60ND	D²PAK	Tape and reel
STF28NM60ND		TO-220FP	Tube
STP28NM60ND		TO-220	
STW28NM60ND		TO-247	

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D^2PAK, TO-220, TO-247	TO-220FP	
V_{DS}	Drain-source voltage	600		V
V_{GS}	Gate-source voltage	±25		V
I_D	Drain current (continuous) at T_C = 25 °C	23	23(1)	A
I_D	Drain current (continuous) at T_C = 100 °C	14.5	14.5(1)	A
I_{DM} (2)	Drain current (pulsed)	92	92(1)	A
P_{TOT}	Total dissipation at T_C = 25 °C	190	35	W
dv/dt(3)	Peak diode recovery voltage slope	40		V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T_C=25 °C)		2500	V
T_{stg}	Storage temperature	–55 to 150		°C
T_J	Max. operating junction temperature	150		°C

1. Limited by maximum junction temperature
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 23$ A, di/dt ≤ 600 A/μs, V_{DD} = 80% $V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	D^2PAK	TO-220FP	TO-220	TO-247	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	0.66	3.6	0.66		°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max		62.5		50	°C/W
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb max	30				°C/W

1. When mounted on 1inch² FR-4 board, 2 oz Cu

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max)	5	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, $I_D = I_{AS}$, V_{DD} = 50 V)	450	mJ

2 Electrical characteristics

(T_{CASE}=25 °C unless otherwise specified).

Table 5. On/off states

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0	600			V
dv/dt(1)	Drain source voltage slope	V_{DD}= 480 V, I_D= 23 A, V_{GS}= 10 V		45		V/ns
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 600 V			1	µA
		V_{DS} = 600 V, T_C= 125 °C			100	µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 20 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10 V, I_D = 11.5 A		0.13	0.15	Ω

1. Characteristic value at turn off on inductive load.

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0	-	2090	-	pF
C_{oss}	Output capacitance		-	90	-	pF
C_{rss}	Reverse transfer capacitance		-	5.5	-	pF
$C_{oss\ eq.}$(1)	Equivalent output capacitance	V_{GS} = 0, V_{DS} = 0 to 480 V	-	312	-	pF
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 11.5 A R_G = 4.7 Ω V_{GS} = 10 V *(see Figure 18)*, *(see Figure 20)*	-	23.5	-	ns
t_r	Rise time		-	21.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	92	-	ns
t_f	Fall time		-	27	-	ns
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 23 A, V_{GS} = 10 V, *(see Figure 10)*	-	62.5	-	nC
Q_{gs}	Gate-source charge		-	11	-	nC
Q_{gd}	Gate-drain charge		-	38	-	nC
R_g	Gate input resistance	f = 1 MHz, test signal level = 20 mV, I_D = 0	-	4.7	-	Ω

1. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		23	A
I_{SDM} (1)	Source-drain current (pulsed)		-		92	A
V_{SD} (2)	Forward on voltage	I_{SD} = 23 A, V_{GS} = 0	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 23 A, V_{DD} = 60 V di/dt=100 A/μs *(see Figure 17)*	-	170		ns
Q_{rr}	Reverse recovery charge		-	1160		nC
I_{RRM}	Reverse recovery current		-	14		A
t_{rr}	Reverse recovery time	I_{SD} = 23 A,V_{DD} = 60 V di/dt=100 A/μs, T_J = 150 °C *(see Figure 17)*	-	237		ns
Q_{rr}	Reverse recovery charge		-	2090		nC
I_{RRM}	Reverse recovery current		-	18		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 μs, duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D²PAK and TO-220

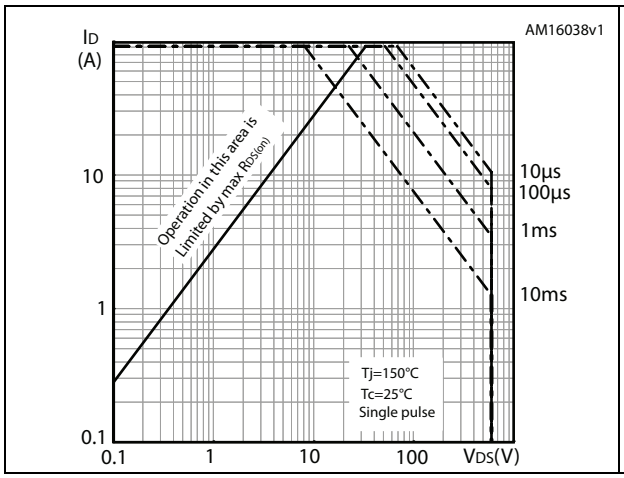


Figure 3. Thermal impedance for D²PAK and TO-220

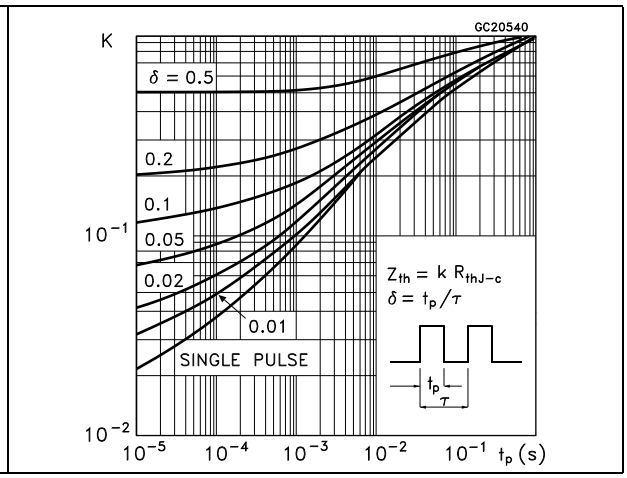


Figure 4. Safe operating area for TO-220FP

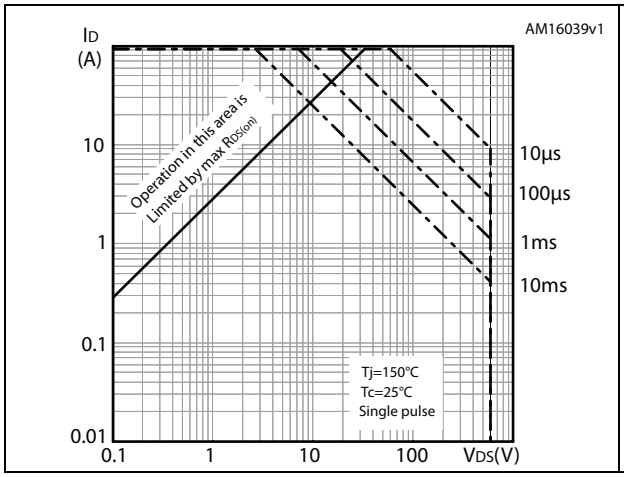


Figure 5. Thermal impedance for TO-220FP

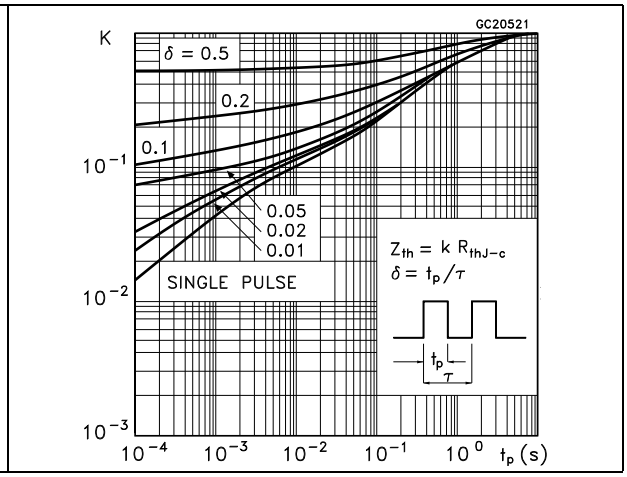


Figure 6. Safe operating area for TO-247

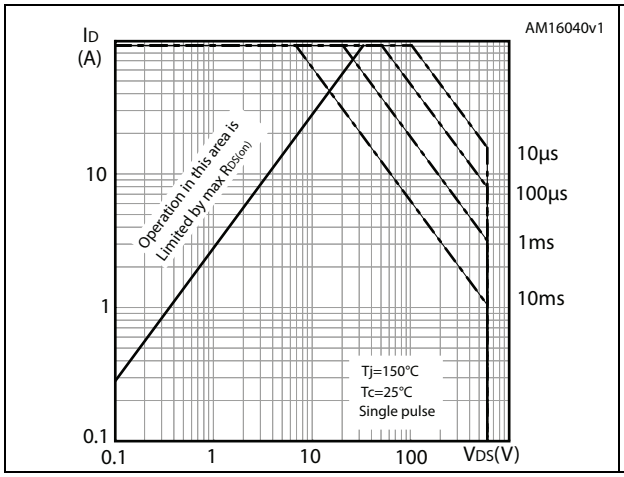


Figure 7. Thermal impedance for TO-247

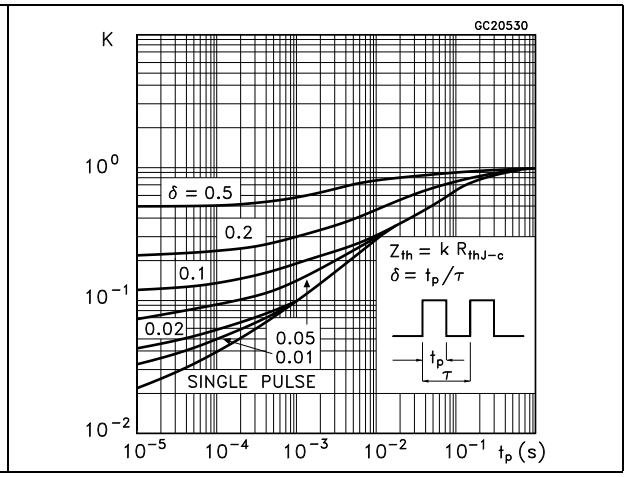


Figure 8. Output characteristics

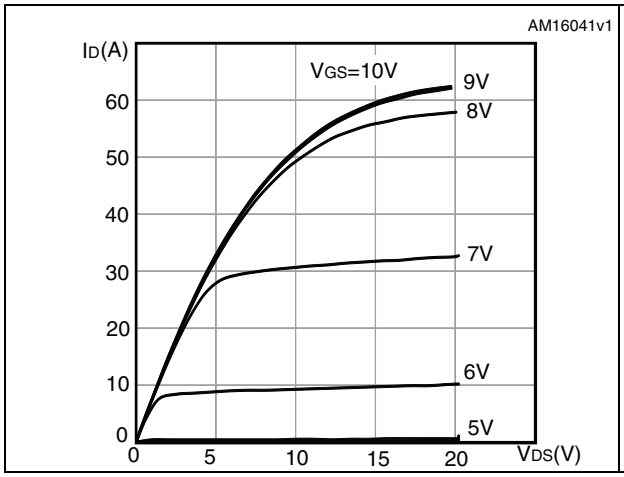


Figure 9. Transfer characteristics

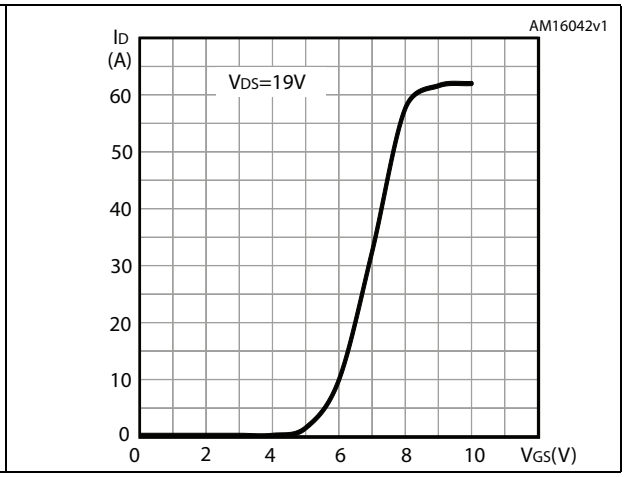


Figure 10. Gate charge vs gate-source voltage

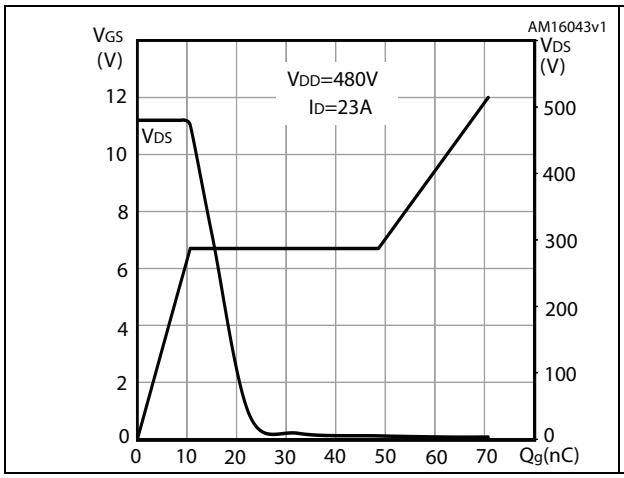


Figure 11. Static drain-source on-resistance

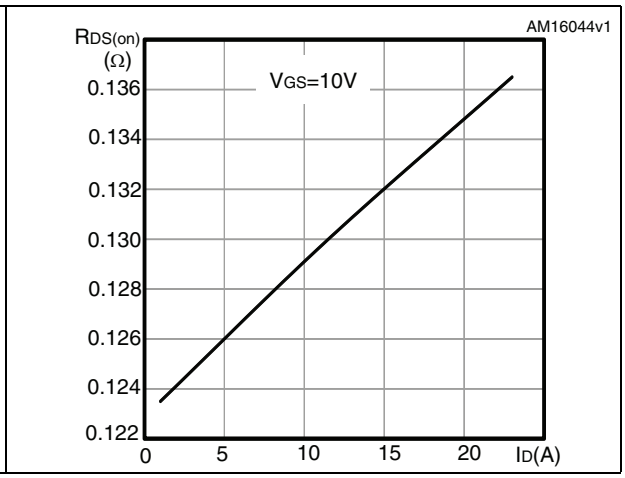


Figure 12. Capacitance variations

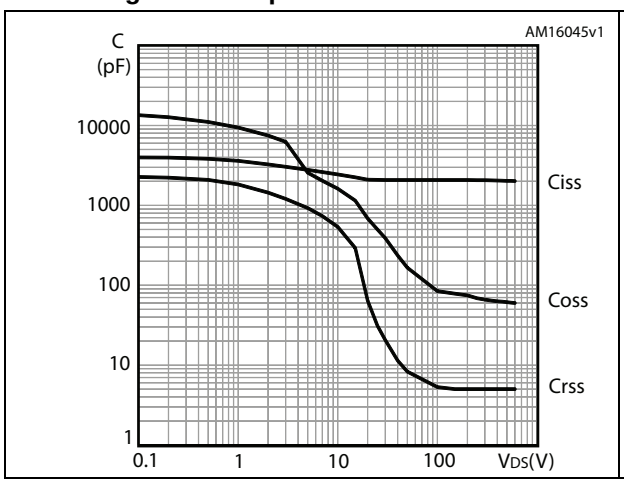


Figure 13. Output capacitance stored energy

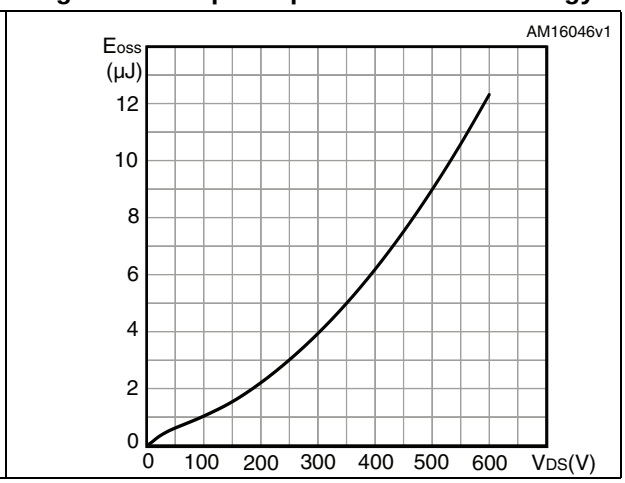


Figure 14. Normalized gate threshold voltage vs temperature

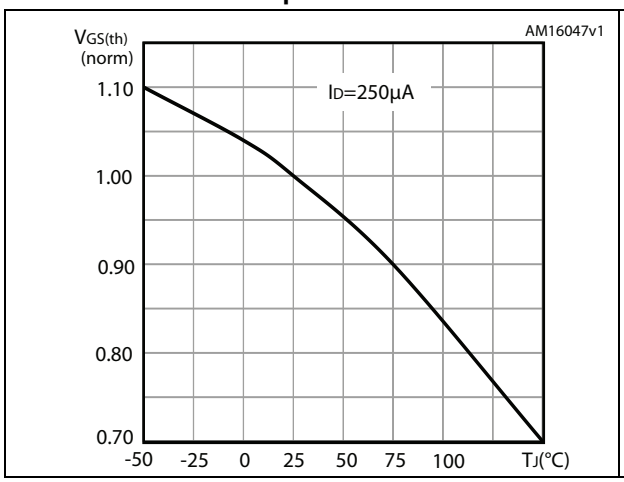


Figure 15. Normalized on-resistance vs temperature

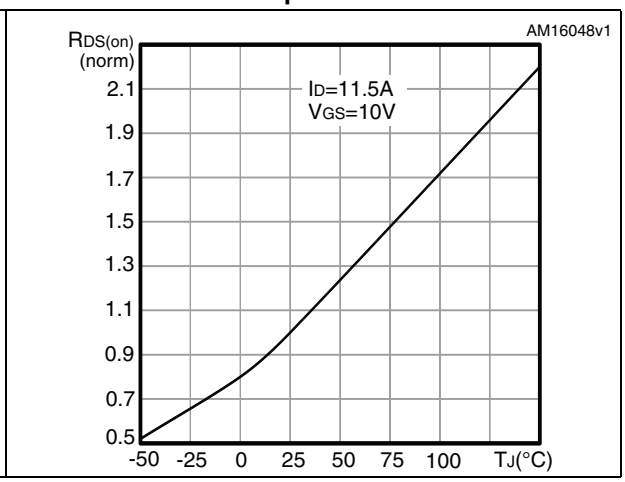


Figure 16. Source-drain diode forward characteristics

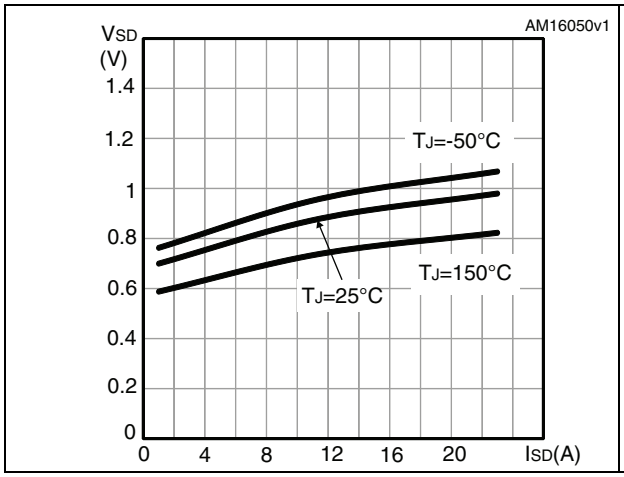
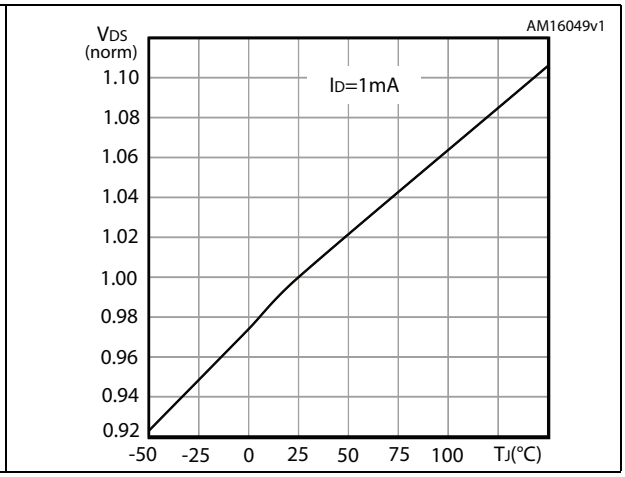


Figure 17. Normalized V_{DS} vs temperature



3 Test circuits

Figure 18. Switching times test circuit for resistive load

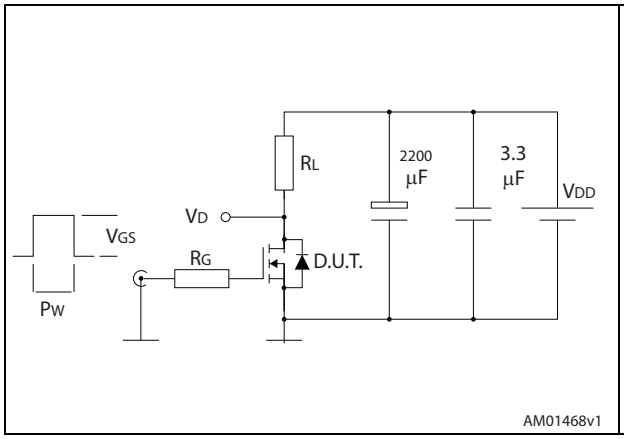


Figure 19. Gate charge test circuit

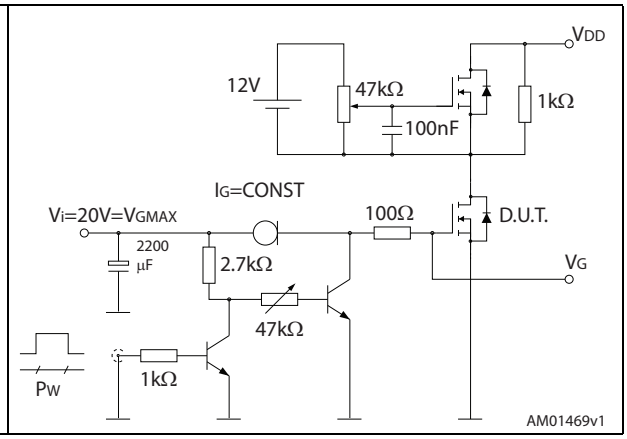


Figure 20. Test circuit for inductive load switching and diode recovery times

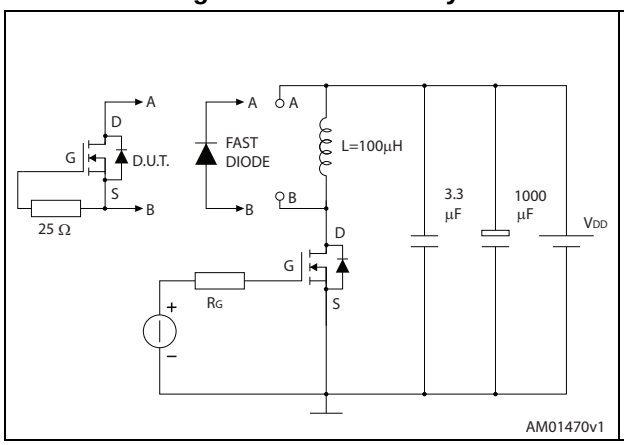


Figure 21. Unclamped inductive load test circuit

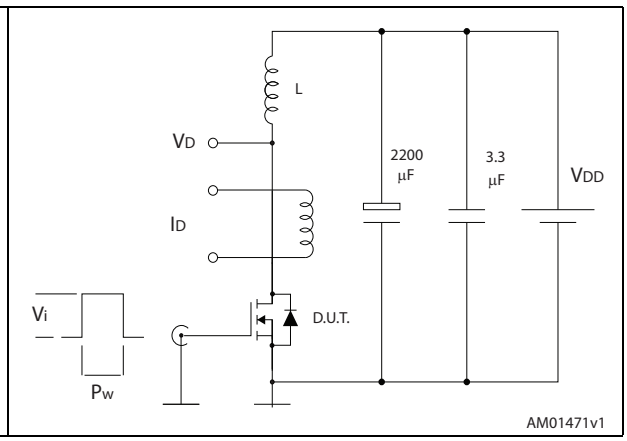


Figure 22. Unclamped inductive waveform

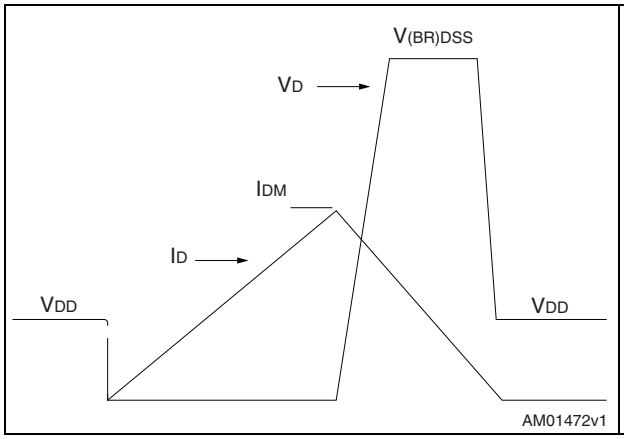
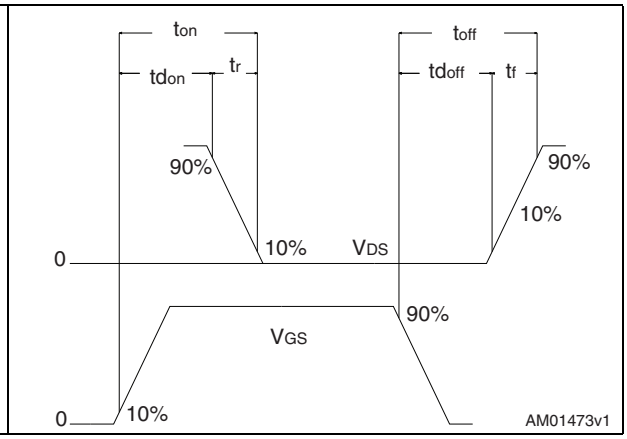


Figure 23. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

4.1 D²PAK, STB28NM60ND

Figure 24. D²PAK (TO-263) drawing

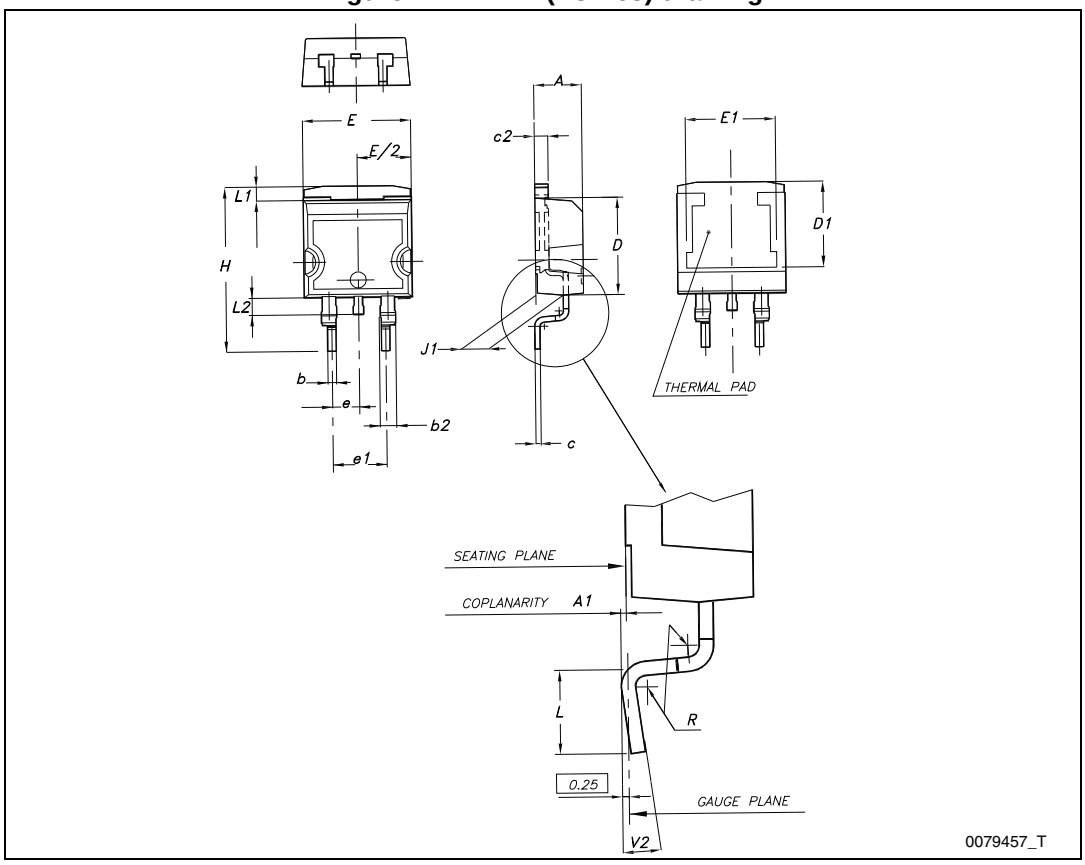
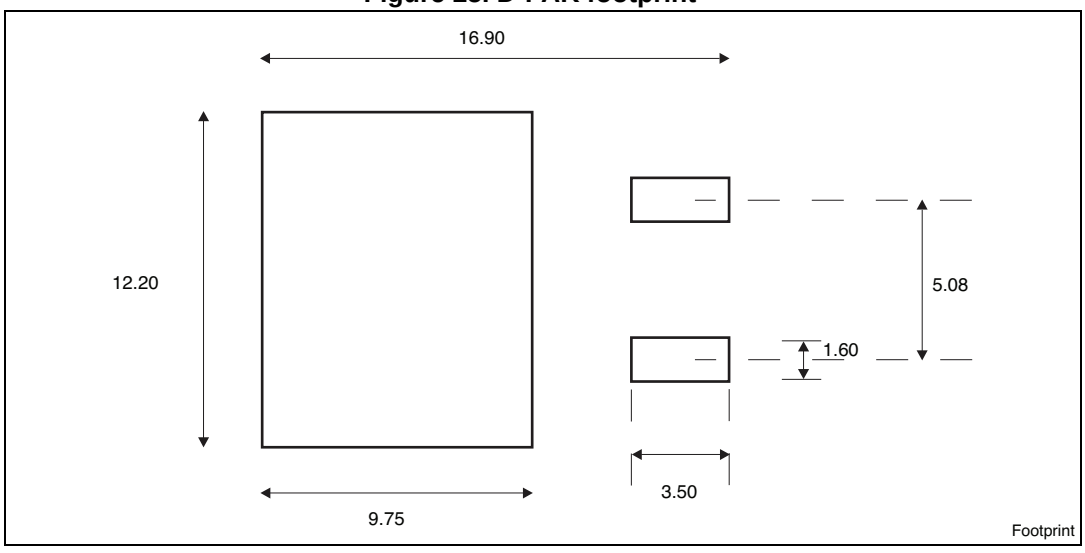


Table 8. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 25. D²PAK footprint[(a)]



a. All dimension are in millimeters

4.2 TO-220FP, STF28NM60ND

Figure 26. TO-220FP drawing

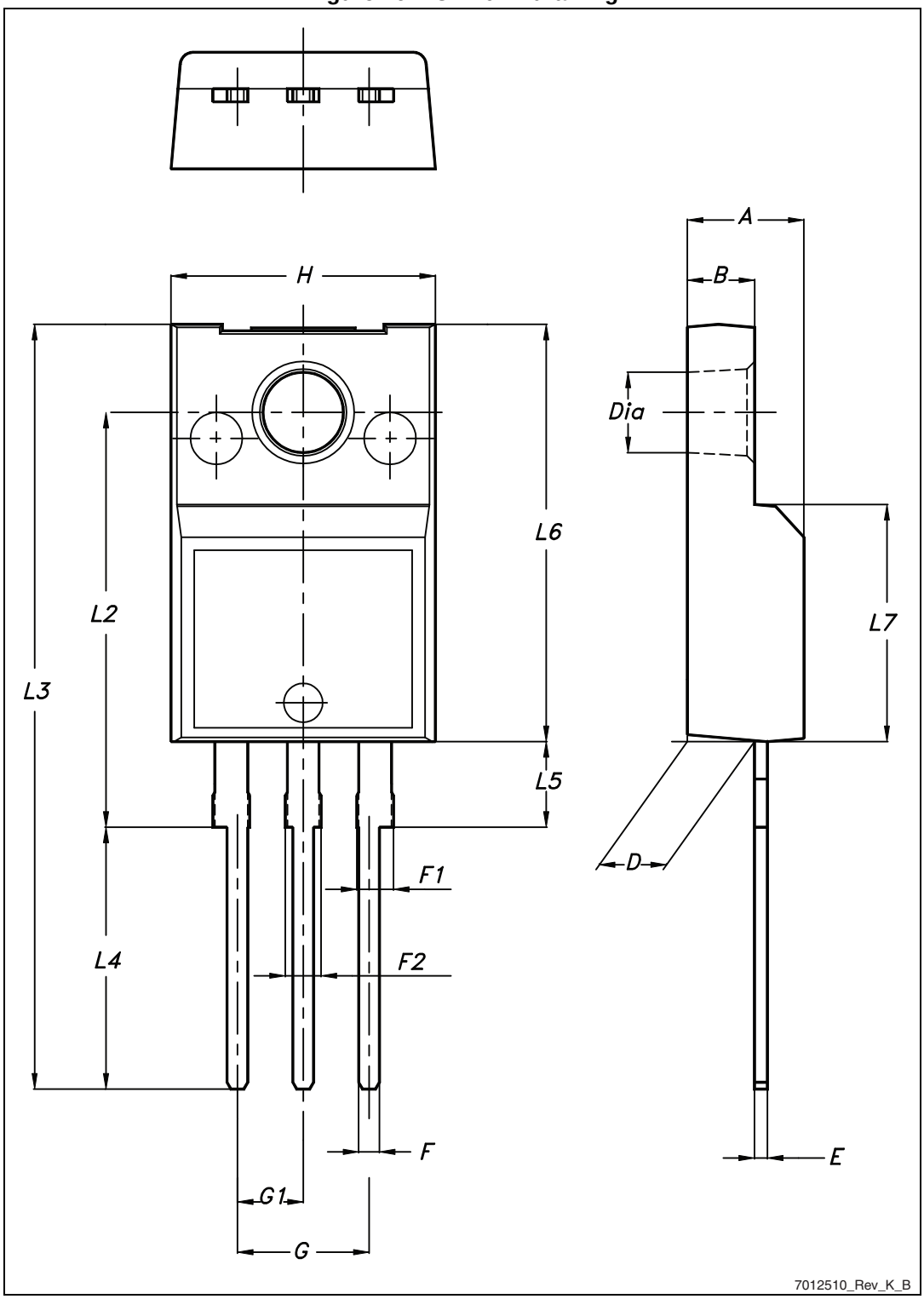


Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

4.3 TO-220, STP28NM60ND

Figure 27. TO-220 type A drawing

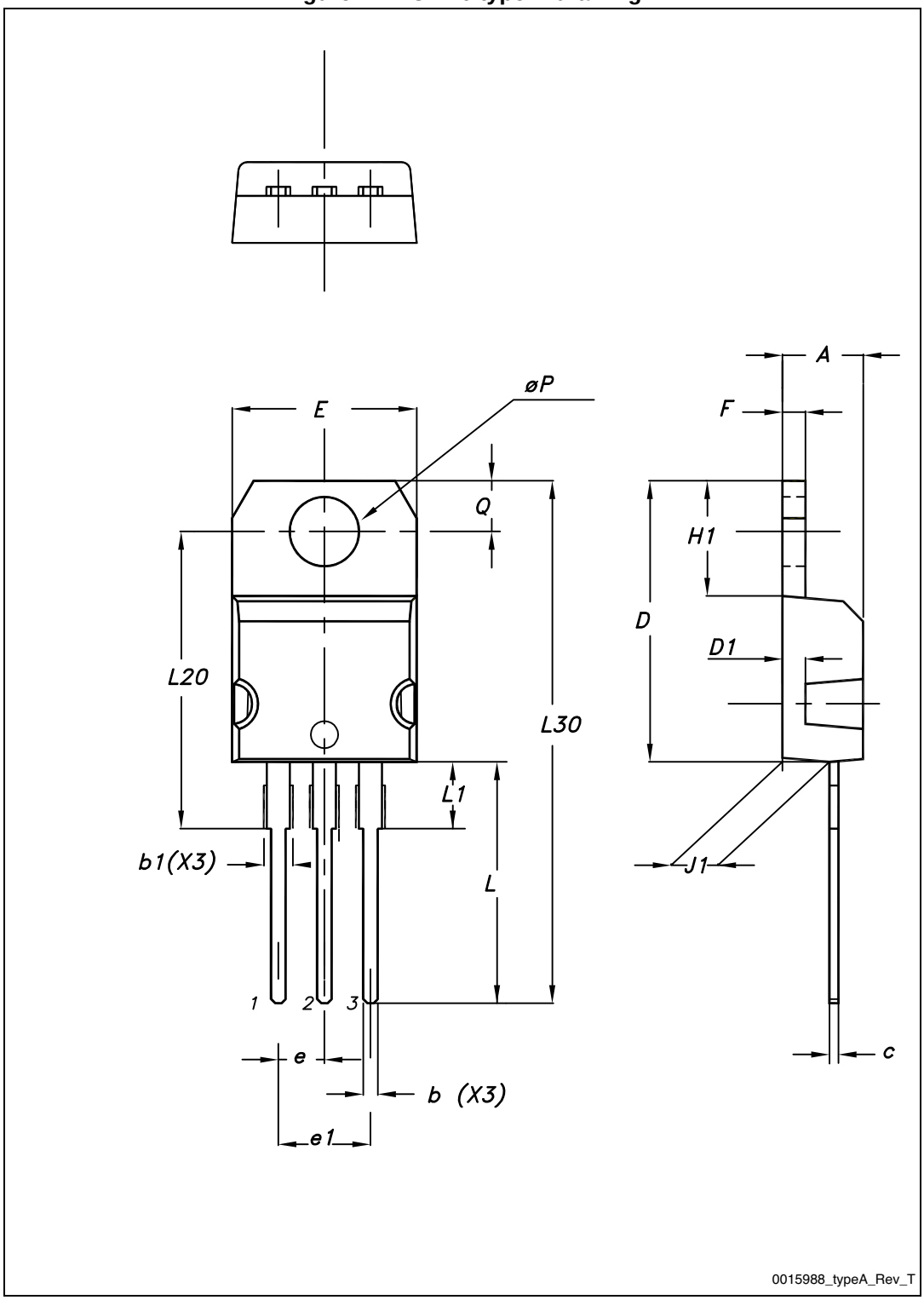


Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95

4.4 TO-247, STW28NM60ND

Figure 28. TO-247 drawing

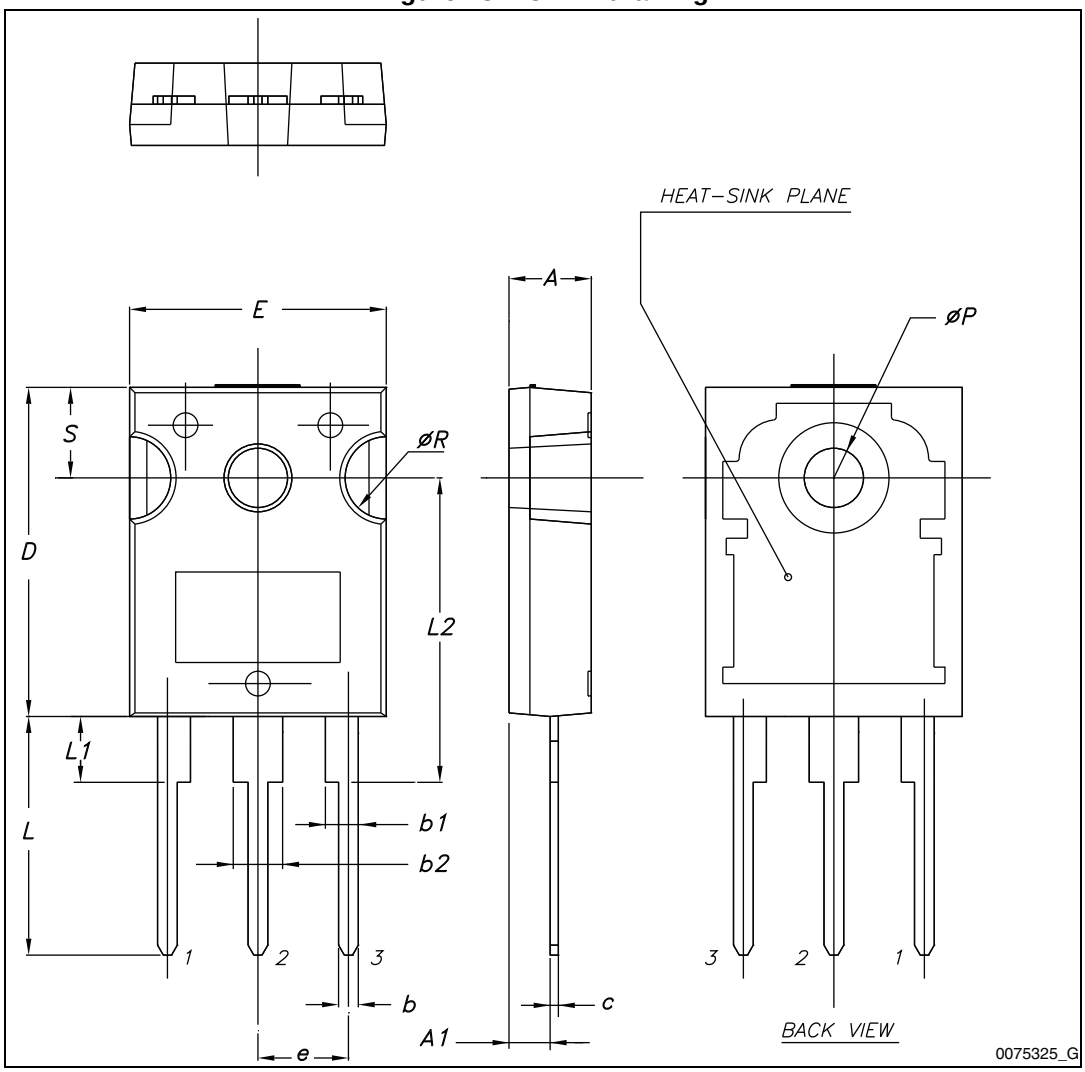


Table 11. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
∅P	3.55		3.65
∅R	4.50		5.50
S	5.30	5.50	5.70

5 Packing mechanical data

Figure 29. Tape

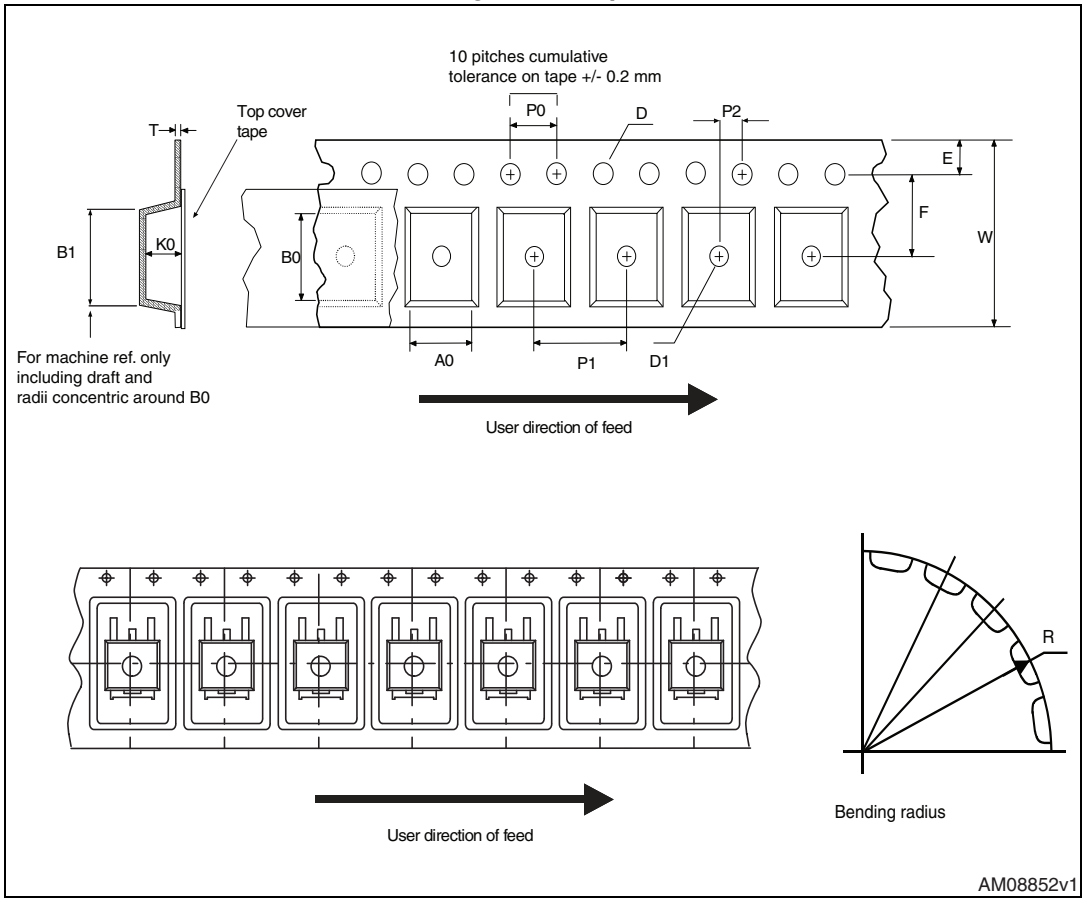
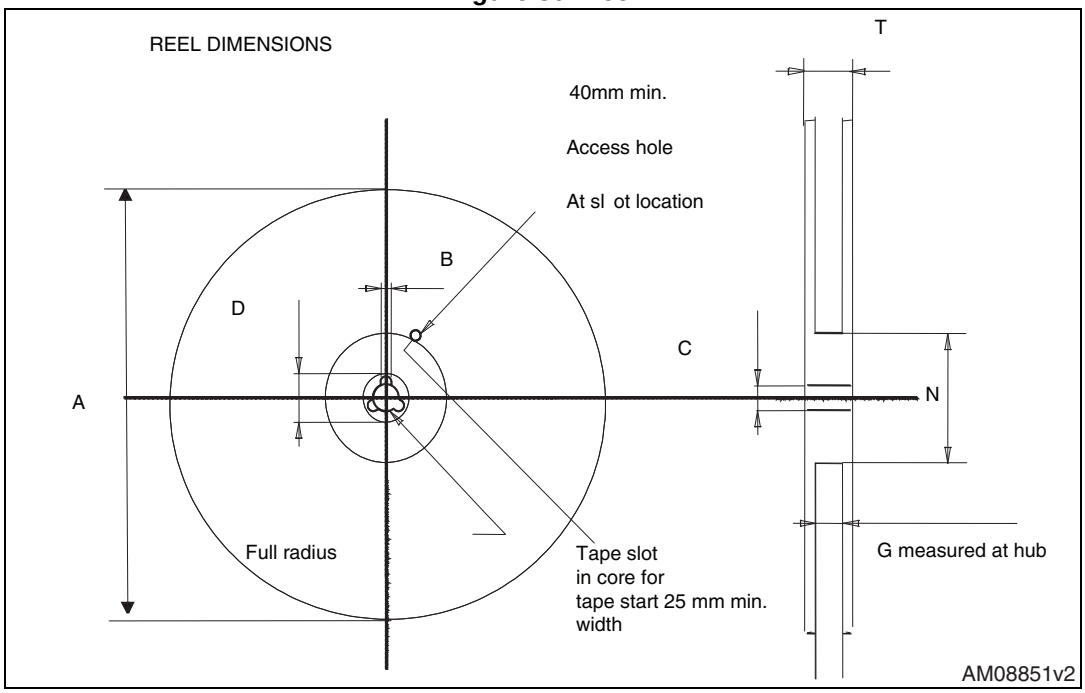


Table 12. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 30. Reel



6 Revision history

Table 13. Document revision history

Date	Revision	Changes
15-Apr-2013	1	First release.
25-Nov-2013	2	– Document status changed from preliminary to production data – Modified: typical values in *Table 6* and *7* – Added: *Section 2.1: Electrical characteristics (curves)* – Updated: *Table 10* and *Figure 27* – Minor text changes
05-May-2014	3	– Modified: E_{AS} value in *Table 4* – Minor text changes

Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

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